

## Electronic Supplementary Material

### **Enhancement of Hall mobility and conductivity of CVD graphene through radical doping and vacuum annealing**

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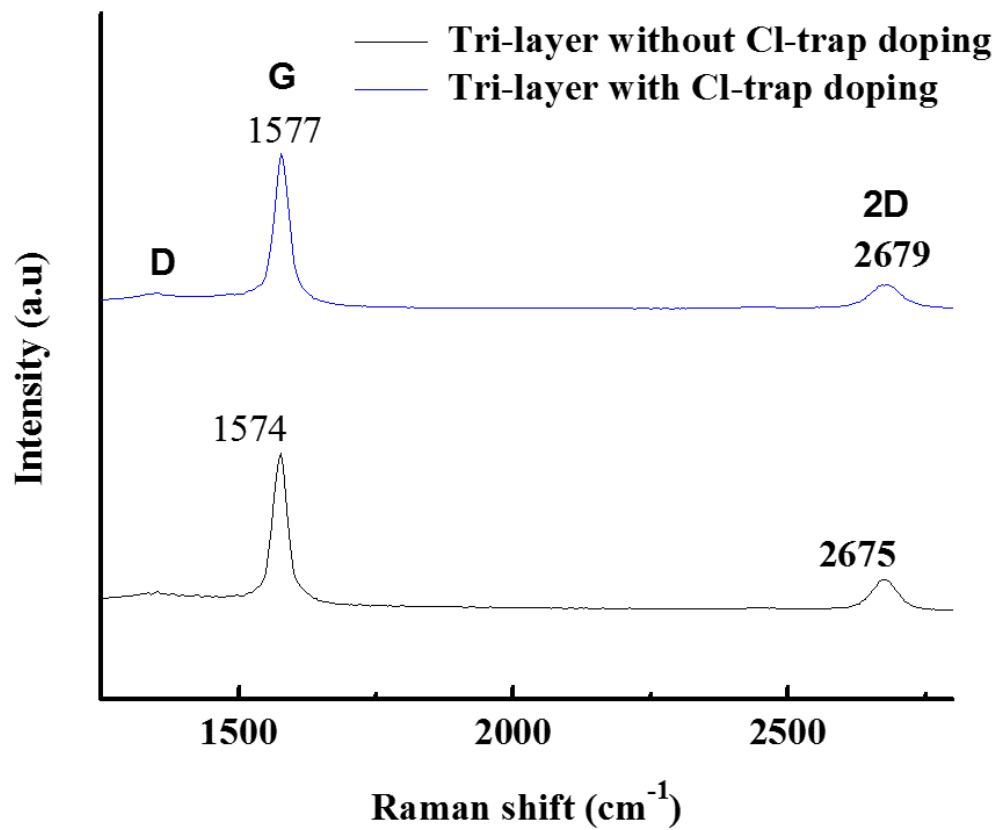


Fig S1. Raman spectra of tri-layer graphene with/without p-type Cl-trap doping.

With Cl-trap doping, tri-layer graphene showed the blue shift of G and 2D peaks, indicating the Cl dopant as a p-type doping on graphene.